Harri Lipsanen

List of Publications by Citations

358 papers	6,404 citations	40 h-index	64 g-index
406 ext. papers	7,349 ext. citations	3.7 avg, IF	5.67 L-index

#	Paper	IF	Citations
358	Nonlinear Optics with 2D Layered Materials. *Advanced Materials*, **2018**, 30, e1705963	24	309
357	Polarization and Thickness Dependent Absorption Properties of Black Phosphorus: New Saturable Absorber for Ultrafast Pulse Generation. *Scientific Reports*, **2015**, 5, 15899	4.9	225
356	Production and processing of graphene and related materials. *2D Materials*, **2020**, 7, 022001	5.9	179
355	Luminescence from excited states in strain-induced InxGa1-xAs quantum dots. *Physical Review B*, **1995**, 51, 13868-13871	3.3	161
354	Crystal-structure-dependent photoluminescence from InP nanowires. *Nanotechnology*, **2006**, 17, 1580-3	3.4	143
353	Ultra-strong nonlinear optical processes and trigonal warping in MoS layers. *Nature Communications*, **2017**, 8, 893	17.4	123
352	Aluminum oxide from trimethylaluminum and water by atomic layer deposition: The temperature dependence of residual stress, elastic modulus, hardness and adhesion. *Thin Solid Films*, **2014**, 552, 124-135	2.2	119
351	Carrier relaxation dynamics in quantum dots: Scattering mechanisms and state-filling effects. *Physical Review B*, **1997**, 55, 4473-4476	3.3	107
350	Dispersion engineering of photonic crystal waveguides with ring-shaped holes. *Optics Express*, **2007**, 15, 8323-8	3.3	102
349	A single-pixel wireless contact lens display. *Journal of Micromechanics and Microengineering*, **2011**, 21, 125014	2	98
348	Rapid visualization of grain boundaries in monolayer MoS by multiphoton microscopy. *Nature Communications*, **2017**, 8, 15714	17.4	93
347	Zeeman Effect in Parabolic Quantum Dots. *Physical Review Letters*, **1996**, 77, 342-345	7.4	92
346	Properties of AlN grown by plasma enhanced atomic layer deposition. *Applied Surface Science*, **2011**, 257, 7827-7830	6.7	91
345	Catalyst-free growth of In(As)P nanowires on silicon. *Applied Physics Letters*, **2006**, 89, 063119	3.4	84
344	Strain-induced quantum dots by self-organized stressors. *Applied Physics Letters*, **1995**, 66, 2364-2366	3.4	82
343	Investigation of second- and third-harmonic generation in few-layer gallium selenide by multiphoton microscopy. *Scientific Reports*, **2015**, 5, 10334	4.9	76
342	Observation of defect complexes containing Ga vacancies in GaAsN. *Applied Physics Letters*, **2003**, 82, 40-42	3.4	76

341	Tunable Graphene-GaSe Dual Heterojunction Device. *Advanced Materials*, **2016**, 28, 1845-52	24	76
340	Black phosphorus polycarbonate polymer composite for pulsed fibre lasers. *Applied Materials Today* , **2016**, 4, 17-23	6.6	74
339	Rapid large-area multiphoton microscopy for characterization of graphene. *ACS Nano*, **2013**, 7, 8441-6	16.7	69
338	High quality GaAs nanowires grown on glass substrates. *Nano Letters*, **2012**, 12, 1912-8	11.5	66
337	Temperature dependence of carrier relaxation in strain-induced quantum dots. *Physical Review B*, **1998**, 58, R15993-R15996	3.3	63
336	Selective growth of InGaAs on nanoscale InP islands. *Applied Physics Letters*, **1994**, 65, 1662-1664	3.4	61
335	A MoSe2/WSe2 Heterojunction-Based Photodetector at Telecommunication Wavelengths. *Advanced Functional Materials*, **2018**, 28, 1804388	15.6	60
334	Self-organized InP islands on (100) GaAs by metalorganic vapor phase epitaxy. *Applied Physics Letters*, **1995**, 67, 3768-3770	3.4	59
333	Ultra-high on-chip optical gain in erbium-based hybrid slot waveguides. *Nature Communications*, **2019**, 10, 432	17.4	57
332	Review Article: Recommended reading list of early publications on atomic layer deposition□Outcome of the □Virtual Project on the History of ALD□*Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2017**, 35, 010801	2.9	55
331	Self-organized InAs islands on (100) InP by metalorganic vapor-phase epitaxy. *Surface Science*, **1997**, 376, 60-68	1.8	55
330	Second-harmonic generation imaging of semiconductor nanowires with focused vector beams. *Nano Letters*, **2015**, 15, 1564-9	11.5	53
329	Optical harmonic generation in monolayer group-VI transition metal dichalcogenides. *Physical Review B*, **2018**, 98,	3.3	53
328	Direct observation of confined acoustic phonon polarization branches in free-standing semiconductor nanowires. *Nature Communications*, **2016**, 7, 13400	17.4	51
327	Rapid and Large-Area Characterization of Exfoliated Black Phosphorus Using Third-Harmonic Generation Microscopy. *Journal of Physical Chemistry Letters*, **2017**, 8, 1343-1350	6.4	50
326	Thermal and plasma enhanced atomic layer deposition of SiO2 using commercial silicon precursors. *Thin Solid Films*, **2014**, 558, 93-98	2.2	50
325	High photoresponsivity and broadband photodetection with a band-engineered WSe/SnSe heterostructure. *Nanoscale*, **2019**, 11, 3240-3247	7.7	49
324	Graphene-enhanced Raman imaging of TiO2 nanoparticles. *Nanotechnology*, **2012**, 23, 465703	3.4	49

323	High nitrogen composition GaAsN by atmospheric pressure metalorganic vapor-phase epitaxy. *Journal of Crystal Growth*, **2000**, 221, 456-460	1.6	48
322	Noncovalent attachment of pyro-pheophorbide a to a carbon nanotube. *Chemical Communications*, **2007**, 519-21	5.8	45
321	Photovoltaic properties of GaAsP core-shell nanowires on Si(001) substrate. *Nanotechnology*, **2012**, 23, 265402	3.4	42
320	Doping and carrier transport in Ga1−xIn3xNxAs1− alloys. *Physical Review B*, **2001**, 64,	3.3	41
319	Second and third harmonic generation in few-layer gallium telluride characterized by multiphoton microscopy. *Applied Physics Letters*, **2016**, 108, 073103	3.4	41
318	Solubility of Boron, Carbon, and Nitrogen in Transition Metals: Getting Insight into Trends from First-Principles Calculations. *Journal of Physical Chemistry Letters*, **2015**, 6, 3263-3268	6.4	40
317	Enhanced luminescence from catalyst-free grown InP nanowires. *Applied Physics Letters*, **2007**, 90, 033101	3.4	39
316	Synthesis of ZnO tetrapods for flexible and transparent UV sensors. *Nanotechnology*, **2012**, 23, 095502	3.4	36
315	GaAs surface passivation by plasma-enhanced atomic-layer-deposited aluminum nitride. *Applied Surface Science*, **2010**, 256, 7434-7437	6.7	36
314	Control of the morphology of InGaN/GaN quantum wells grown by metalorganic chemical vapor deposition. *Journal of Crystal Growth*, **2007**, 300, 324-329	1.6	36
313	Effect of substrate orientation on the catalyst-free growth of InP nanowires. *Nanotechnology*, **2007** , 18, 155301	3.4	35
312	Transformation of self-assembled InAs/InP quantum dots into quantum rings without capping. *Nano Letters*, **2005**, 5, 1541-3	11.5	35
311	Mechanistic investigation of ZnO nanowire growth. *Applied Physics Letters*, **2009**, 95, 183114	3.4	34
310	Synchrotron radiation x-ray topography and defect selective etching analysis of threading dislocations in GaN. *Journal of Applied Physics*, **2014**, 116, 083504	2.5	33
309	Self-Assembled Porphyrins on Modified Zinc Oxide Nanorods: Development of Model Systems for Inorganic−Organic Semiconductor Interface Studies. *Journal of Physical Chemistry C*, **2012**, 116, 2336-2343	3.8	33
308	Magneto-optical properties of strain-induced InxGa1−As parabolic quantum dots. *Physical Review B*, **1998**, 57, 9763-9769	3.3	33
307	Nanowire network-based multifunctional all-optical logic gates. *Science Advances*, **2018**, 4, eaar7954	14.3	30
306	Electrical measurement of internal quantum efficiency and extraction efficiency of III-N light-emitting diodes. *Applied Physics Letters*, **2012**, 101, 021113	3.4	30

305	Enhanced optical properties of in situ passivated near-surface AlxGa1−xAs/GaAs quantum wells. *Applied Physics Letters*, **1996**, 68, 2216-2218	3.4	30
304	Graphene actively Q-switched lasers. *2D Materials*, **2017**, 4, 025095	5.9	29
303	Crystal quality of two-dimensional gallium telluride and gallium selenide using Raman fingerprint. *AIP Advances*, **2017**, 7, 015014	1.5	29
302	Photo-thermal chemical vapor deposition of graphene on copper. *Carbon*, **2013**, 62, 43-50	10.4	29
301	Pauli-blocking imaging of single strain-induced semiconductor quantum dots. *Applied Physics Letters*, **1999**, 74, 3200-3202	3.4	29
300	Aluminum oxide/titanium dioxide nanolaminates grown by atomic layer deposition: Growth and mechanical properties. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2017**, 35, 01B105	2.9	28
299	Effects of few-particle interaction on the atomiclike levels of a single strain-induced quantum dot. *Physical Review B*, **2000**, 62, 1592-1595	3.3	28
298	Influence of plasma chemistry on impurity incorporation in AlN prepared by plasma enhanced atomic layer deposition. *Journal Physics D: Applied Physics*, **2013**, 46, 505502	3	27
297	Capillary-driven self-assembly of microchips on oleophilic/oleophobic patterned surface using adhesive droplet in ambient air. *Applied Physics Letters*, **2011**, 99, 034104	3.4	27
296	Growth of GaInAsSb using tertiarybutylarsine as arsenic source. *Journal of Crystal Growth*, **1994**, 145, 492-497	1.6	27
295	Direct transfer of wafer-scale graphene films. *2D Materials*, **2017**, 4, 035004	5.9	26
294	Interference effects in photoreflectance of epitaxial layers grown on semi-insulating substrates. *Applied Physics Letters*, **1993**, 63, 2863-2865	3.4	26
293	Low Temperature Growth GaAs on Ge. *Japanese Journal of Applied Physics*, **2005**, 44, 7777-7784	1.4	25
292	X-ray reflectivity characterization of atomic layer deposition Al2O3/TiO2 nanolaminates with ultrathin bilayers. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2014**, 32, 01A111	2.9	24
291	Properties, applications and fabrication of photonic crystals with ring-shaped holes in silicon-on-insulator. *Photonics and Nanostructures - Fundamentals and Applications*, **2008**, 6, 42-46	2.6	24
290	Single-photon sources with quantum dots in III-V nanowires. *Nanophotonics*, **2019**, 8, 747-769	6.3	23
289	Aluminum-Induced photoluminescence red shifts in core-shell GaAs/Al(x)Ga(1-x)As nanowires. *Nano Letters*, **2013**, 13, 3581-8	11.5	23
288	GaInNAs quantum well structures for 1.55 μm emission on GaAs by atmospheric pressure metalorganic vapor phase epitaxy. *Journal of Crystal Growth*, **2002**, 234, 631-636	1.6	23

287	Room-temperature observation of impurity states in bulk GaAs by photoreflectance. *Journal of Applied Physics*, **1989**, 65, 2556-2557	2.5	23
286	Corrosion protection of steel with multilayer coatings: Improving the sealing properties of physical vapor deposition CrN coatings with Al 2 O 3 /TiO 2 atomic layer deposition nanolaminates. *Thin Solid Films*, **2017**, 627, 59-68	2.2	22
285	Young's Modulus of Wurtzite and Zinc Blende InP Nanowires. *Nano Letters*, **2017**, 17, 3441-3446	11.5	22
284	A physics-based model of gate-tunable metal–graphene contact resistance benchmarked against experimental data. *2D Materials*, **2015**, 2, 025006	5.9	22
283	Strong surface passivation of GaAs nanowires with ultrathin InP and GaP capping layers. *Applied Physics Letters*, **2014**, 105, 033114	3.4	22
282	Impurity breakdown and terahertz luminescence in n-GaN epilayers under external electric field. *Journal of Applied Physics*, **2009**, 106, 123523	2.5	21
281	Slow light propagation in photonic crystal waveguides with ring-shaped holes. *Journal of Optics*, **2007**, 9, S415-S418		21
280	Effect of growth conditions on electrical properties of Mg-doped p-GaN. *Journal of Crystal Growth*, **2007**, 298, 811-814	1.6	21
279	Passivation of GaAs surface by ultrathin epitaxial GaN layer. *Journal of Crystal Growth*, **2004**, 272, 621-626	1.6	21
278	. *IEEE Photonics Technology Letters*, **1992**, 4, 673-675	2.2	21
277	Large-area analysis of dislocations in ammonothermal GaN by synchrotron radiation X-ray topography. *Applied Physics Express*, **2014**, 7, 091003	2.4	20
276	Nonlinear microscopy using cylindrical vector beams: Applications to three-dimensional imaging of nanostructures. *Optics Express*, **2017**, 25, 12463-12468	3.3	20
275	Impact of ALD grown passivation layers on silicon nitride based integrated optic devices for very-near-infrared wavelengths. *Optics Express*, **2014**, 22, 5684-92	3.3	20
274	Surface-tension driven self-assembly of microchips on hydrophobic receptor sites with water using forced wetting. *Applied Physics Letters*, **2012**, 101, 114105	3.4	20
273	The effect of InGaN/GaN MQW hydrogen treatment and threading dislocation optimization on GaN LED efficiency. *Journal of Crystal Growth*, **2007**, 298, 740-743	1.6	20
272	Morphology optimization of MOCVD-grown GaN nucleation layers by the multistep technique. *Journal of Crystal Growth*, **2006**, 292, 26-32	1.6	20
271	Structural and chemical analysis of annealed plasma-enhanced atomic layer deposition aluminum nitride films. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2016**, 34, 041506	2.9	20
270	Tailorable second-harmonic generation from an individual nanowire using spatially phase-shaped beams. *Laser and Photonics Reviews*, **2017**, 11, 1600175	8.3	19

269	Enhanced electroluminescence in 405nm InGaN/GaN LEDs by optimized electron blocking layer. *Journal of Crystal Growth*, **2008**, 310, 5154-5157	1.6	19
268	Experimental investigation towards a periodically pumped single-photon source. *Physical Review B*, **2006**, 74,	3.3	19
267	Atomic Layer Engineering of Er-Ion Distribution in Highly Doped Er:Al2O3 for Photoluminescence Enhancement. *ACS Photonics*, **2016**, 3, 2040-2048	6.3	19
266	High-quality crystallinity controlled ALD TiO2 for waveguiding applications. *Optics Letters*, **2013**, 38, 3980-3	3	18
265	Atomic layer deposition of ytterbium oxide using -diketonate and ozone precursors. *Applied Surface Science*, **2009**, 256, 847-851	6.7	18
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263	Growth of high-quality GaSb by metalorganic vapor phase epitaxy. *Journal of Electronic Materials*, **1995**, 24, 1691-1696	1.9	18
262	Superhydrophobic Antireflection Coating on Glass Using Grass-like Alumina and Fluoropolymer. *ACS Applied Materials & Interfaces*, **2020**, 12, 49957-49962	9.5	18
261	Protective capping and surface passivation of III-V nanowires by atomic layer deposition. *AIP Advances*, **2016**, 6, 015016	1.5	18
260	Effect of growth temperature on the epitaxial growth of ZnO on GaN by ALD. *Journal of Crystal Growth*, **2014**, 398, 18-22	1.6	17
259	Demonstration of longitudinally polarized optical needles. *Optics Express*, **2018**, 26, 27572-27584	3.3	17
258	Passivation of GaAs surface by atomic-layer-deposited titanium nitride. *Applied Surface Science*, **2008**, 254, 5385-5389	6.7	16
257	Genetic algorithm using independent component analysis in x-ray reflectivity curve fitting of periodic layer structures. *Journal Physics D: Applied Physics*, **2007**, 40, 6000-6004	3	16
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255	Multistep method for threading dislocation density reduction in MOCVD grown GaN epilayers. *Physica Status Solidi (A) Applications and Materials Science*, **2006**, 203, R76-R78	1.6	16
254	Electron-Hole Correlation in Quantum Dots under a High Magnetic Field (up to 45 T). *Physical Review Letters*, **1999**, 83, 4832-4835	7.4	16
253	Metalorganic vapor phase epitaxial growth of AlGaSb and AlGaAsSb using all-organometallic sources. *Journal of Crystal Growth*, **1996**, 169, 417-423	1.6	16
252	Red luminescence from strain-induced GaInP quantum dots. *Applied Physics Letters*, **1996**, 69, 3393-3395	3.4	16

251	Thermal conductivity of amorphous Al2O3/TiO2 nanolaminates deposited by atomic layer deposition. *Nanotechnology*, **2016**, 27, 445704	3.4	16
250	Atomic layer deposition of AlN from AlCl3 using NH3 and Ar/NH3 plasma. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2018**, 36, 021508	2.9	15
249	Surface-Tension-Driven Self-Alignment of Microchips on Black-Silicon-Based Hybrid Template in Ambient Air. *Journal of Microelectromechanical Systems*, **2013**, 22, 739-746	2.5	15
248	Generation of terahertz radiation in ordered arrays of GaAs nanowires. *Applied Physics Letters*, **2015**, 106, 252104	3.4	15
247	Metal Contacts on InN: Proposal for Schottky Contact. *Japanese Journal of Applied Physics*, **2006**, 45, 36-39	1.4	15
246	Self-assembled GaIn(N)As quantum dots: Enhanced luminescence at 1.3 μm. *Applied Physics Letters*, **2001**, 79, 3932-3934	3.4	15
245	Mechanical nanomanipulation of single strain-induced semiconductor quantum dots. *Applied Physics Letters*, **1999**, 75, 358-360	3.4	15
244	Direct Growth of Light-Emitting III-V Nanowires on Flexible Plastic Substrates. *ACS Nano*, **2020**, 14, 7484-7491	16.7	14
243	Low-height sharp edged patterns for capillary self-alignment assisted hybrid microassembly. *Journal of Micro-Bio Robotics*, **2014**, 9, 1-10	1.4	14
242	Enhanced Tunneling in a Hybrid of Single-Walled Carbon Nanotubes and Graphene. *ACS Nano*, **2019**, 13, 11522-11529	16.7	13
241	Photoresponse of Graphene-Gated Graphene-GaSe Heterojunction Devices. *ACS Applied Nano Materials*, **2018**, 1, 3895-3902	5.6	13
240	Improved SERS Intensity from Silver-Coated Black Silicon by Tuning Surface Plasmons. *Advanced Materials Interfaces*, **2014**, 1, 1300008	4.6	13
239	Analysis of threading dislocations in void shape controlled GaN re-grown on hexagonally patterned mask-less GaN. *Journal of Crystal Growth*, **2012**, 344, 59-64	1.6	13
238	Ultrafast Relaxation Dynamics in Strain-Induced Quantum Dots. *Physica Status Solidi (B): Basic Research*, **1997**, 204, 251-254	1.3	13
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236	Fabrication and photoluminescence of quantum dots induced by strain of self-organized stressors. *Solid-State Electronics*, **1996**, 40, 601-604	1.7	13
235	Erbium-doped hybrid waveguide amplifiers with net optical gain on a fully industrial 300 mm silicon nitride photonic platform. *Optics Express*, **2020**, 28, 27919-27926	3.3	13
234	Review of fabrication methods of large-area transparent graphene electrodes for industry. *Frontiers of Optoelectronics*, **2020**, 13, 91-113	2.8	13

233	All-Graphene Three-Terminal-Junction Field-Effect Devices as Rectifiers and Inverters. *ACS Nano*, **2015**, 9, 5666-74	16.7	12
232	Spontaneous and stimulated emission in InAsSb-based LED heterostructures. *Infrared Physics and Technology*, **2017**, 85, 246-250	2.7	12
231	Nonlinear behavior of three-terminal graphene junctions at room temperature. *Nanotechnology*, **2012**, 23, 115201	3.4	12
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229	Ferromagnetic (Ga,Mn)As nanowires grown by Mn-assisted molecular beam epitaxy. *Journal of Applied Physics*, **2013**, 113, 144303	2.5	12
228	InGaN-based 405 nm near-ultraviolet light emitting diodes on pillar patterned sapphire substrates. *CrystEngComm*, **2010**, 12, 3152	3.3	12
227	Void shape control in GaN re-grown on hexagonally patterned mask-less GaN. *Journal of Crystal Growth*, **2011**, 315, 188-191	1.6	12
226	MOVPE growth and characterization of InAlGaN films and InGaN/InAlGaN MQW structures. *Journal of Crystal Growth*, **2008**, 310, 1777-1780	1.6	12
225	Comparison of epitaxial thin layer GaN and InP passivations on InGaAs□GaAs near-surface quantum wells. *Applied Physics Letters*, **2006**, 88, 221112	3.4	12
224	Photoreflectance study of photovoltage effects in GaAs diode structures. *Applied Physics Letters*, **1992**, 60, 2110-2112	3.4	12
223	Slot waveguide ring resonators coated by an atomic layer deposited organic/inorganic nanolaminate. *Optics Express*, **2015**, 23, 26940-51	3.3	11
222	Nanotribological, nanomechanical and interfacial characterization of atomic layer deposited TiO2 on a silicon substrate. *Wear*, **2015**, 342-343, 270-278	3.5	11
221	Effect of Surface Wear on Corrosion Protection of Steel by CrN Coatings Sealed with Atomic Layer Deposition. *ACS Omega*, **2018**, 3, 1791-1800	3.9	11
220	Identifying threading dislocation types in ammonothermally grown bulk □GaN by confocal Raman 3-D imaging of volumetric stress distribution. *Journal of Crystal Growth*, **2018**, 499, 47-54	1.6	11
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214	Stress distribution of GaN layer grown on micro-pillar patterned GaN templates. *Applied Physics Letters*, **2013**, 103, 012102	3.4	11
213	Growth temperature dependence of the electrical and structural properties of epitaxial graphene on SiC(0001). *Physica Status Solidi (B): Basic Research*, **2011**, 248, 1908-1914	1.3	11
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211	Influence of substrate temperature on the shape of GaAs nanowires grown by Au-assisted MOVPE. *Journal of Crystal Growth*, **2010**, 312, 1676-1682	1.6	11
210	Aluminum Nitride Transition Layer for Power Electronics Applications Grown by Plasma-Enhanced Atomic Layer Deposition. *Materials*, **2019**, 12,	3.5	10
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203	Structural and optical properties of GaInNAs/GaAs quantum structures. *Journal of Physics Condensed Matter*, **2004**, 16, S3009-S3026	1.8	10
202	Misfit dislocations in GaAsN/GaAs interface. *Journal of Materials Science: Materials in Electronics*, **2003**, 14, 267-270	2.1	10
201	Influence of surface passivation on electric properties of individual GaAs nanowires studied by current□oltage AFM measurements. *Lithuanian Journal of Physics*, **2016**, 56,	1.1	10
200	Nanowire encapsulation with polymer for electrical isolation and enhanced optical properties. *Nano Research*, **2017**, 10, 2657-2666	10	9
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197	A technique for large-area position-controlled growth of GaAs nanowire arrays. *Nanotechnology*, **2016**, 27, 135601	3.4	9
196	Substitutionality of nitrogen atoms and formation of nitrogen complexes and point defects in GaPN alloys. *Journal Physics D: Applied Physics*, **2014**, 47, 075106	3	9
195	Growth and characterization of GaP layers on silicon substrates by metal-organic vapour phase epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 1607-1609		9
194	Patterning of sapphire/GaN substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 1509-1512		9
193	Reduced photoluminescence from InGaN/GaN multiple quantum well structures following 40Mev iodine ion irradiation. *Physica B: Condensed Matter*, **2009**, 404, 4925-4928	2.8	9
192	Inhomogeneous Barrier Height Analysis of (Ni/Au)□hAlGaN/GaN Schottky Barrier Diode. *Japanese Journal of Applied Physics*, **2011**, 50, 030201	1.4	9
191	Comparison of ammonia plasma and AlN passivation by plasma-enhanced atomic layer deposition. *Journal of Applied Physics*, **2012**, 111, 063511	2.5	9
190	Structural study of GaP layers on misoriented silicon (001) substrates by transverse scan analysis. *Journal of Applied Physics*, **2012**, 111, 043518	2.5	9
189	Carrier Relaxation in (GaIn)As Quantum Dots. *Physica Status Solidi A*, **1997**, 164, 421-425		9
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186	Fabrication of dual-type nanowire arrays on a single substrate. *Nano Letters*, **2015**, 15, 1679-83	11.5	8
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180	Tailoring of Energy Levels in Strain-Induced Quantum Dots. *Japanese Journal of Applied Physics*, **1999**, 38, 1081-1084	1.4	8

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